

**描述 / Descriptions**

TO-263 塑封封装 N 沟道场效应管。

N-CHANNEL MOSFET in a TO-263 Plastic Package.

**特征 / Features**

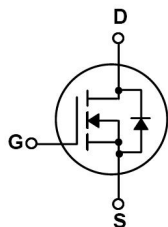
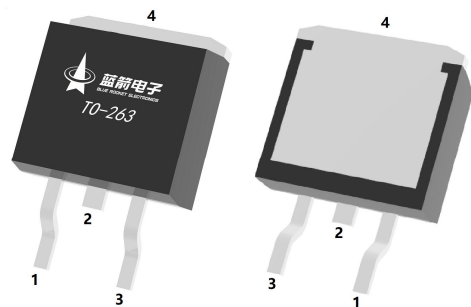
低电阻,开关速度快,无卤产品。

Ultra Low On-Resistance,fast switching,HF Product.

**用途 / Applications**

高频开关和同步整流、BMS、电机。

High frequency switching and synchronous rectification,BMS,Motor.

**内部等效电路 / Equivalent Circuit****引脚排列 / Pinning**

PIN1 : G

PIN 2、 4 : D

PIN 3 : S

**印章代码 / Marking**

见印章说明。 See Marking Instructions.

**极限参数 / Absolute Maximum Ratings(Ta=25°C)**

| 参数<br>Parameter                         |              | 符号<br>Symbol                      | 数值<br>Rating | 单位<br>Unit |
|-----------------------------------------|--------------|-----------------------------------|--------------|------------|
| Drain-Source Voltage                    |              | V <sub>DSS</sub>                  | 100          | V          |
| Drain Current                           |              | I <sub>D</sub> (Tc=25℃)           | 180          | A          |
| Pulsed Drain Current                    |              | I <sub>DM</sub>                   | 385          | A          |
| Gate-Source Voltage                     |              | V <sub>GS</sub>                   | ±20          | V          |
| Single Pulsed Avalanche Energy(L=0.5mH) |              | E <sub>AS</sub>                   | 563          | mJ         |
| Avalanche Current                       |              | I <sub>AS</sub>                   | 37.5         | A          |
| Total Power Dissipation                 |              | P <sub>D</sub> (Tc=25℃)           | 237          | W          |
| Junction and Storage Temperature Range  |              | T <sub>J</sub> , T <sub>STG</sub> | -55 to 150   | ℃          |
| Thermal Resistance-Junction to Ambient  | t≤10s        | R <sub>θJA</sub>                  | 17.7         | ℃/W        |
|                                         | Steady-State |                                   | 70.7         |            |
| Thermal Resistance-Junction to Case     | Steady-State | R <sub>θJC</sub>                  | 0.53         |            |

**电性能参数 / Electrical Characteristics(Ta=25°C)**

| 参数<br>Parameter                   | 符号<br>Symbol | 测试条件<br>Test Conditions                                    | 最小值<br>Min | 典型值<br>Typ | 最大值<br>Max | 单位<br>Unit    |
|-----------------------------------|--------------|------------------------------------------------------------|------------|------------|------------|---------------|
| Drain-Source Breakdown Voltage    | $BV_{DSS}$   | $V_{GS}=0\text{V}$ $I_D=250\mu\text{A}$                    | 100        | 112        |            | V             |
| Zero Gate Voltage Drain Current   | $I_{DSS}$    | $V_{DS}=100\text{V}$ $V_{GS}=0\text{V}$                    |            |            | 1          | $\mu\text{A}$ |
| Gate-Body Leakage Current Forward | $I_{GSS}$    | $V_{GS}=\pm 20\text{V}$ $V_{DS}=0\text{V}$                 |            |            | $\pm 100$  | nA            |
| Gate Threshold Voltage            | $V_{GS(th)}$ | $V_{DS}=V_{GS}$ $I_D=250\mu\text{A}$                       | 2          | 2.9        | 4          | V             |
| Static Drain-Source On-Resistance | $R_{DS(on)}$ | $V_{GS}=10\text{V}$ $I_D=20\text{A}$                       |            | 3.5        | 4.0        | m $\Omega$    |
| Forward On Voltage                | $V_{SD}$     | $V_{GS}=0\text{V}$ $I_S=1\text{A}$                         |            |            | 1.2        | V             |
| Gate resistance                   | $R_g$        | $f=1\text{MHz}$                                            |            | 1.7        |            | $\Omega$      |
| Input Capacitance                 | $C_{iss}$    | $V_{DS}=25\text{V}$ $V_{GS}=0\text{V}$<br>$f=1\text{MHz}$  |            | 5550       |            | pF            |
| Output Capacitance                | $C_{oss}$    |                                                            |            | 2050       |            |               |
| Reverse Transfer Capacitance      | $C_{rss}$    |                                                            |            | 180        |            |               |
| Total Gate Charge                 | $Q_{g(10V)}$ | $V_{GS}=10\text{V}$ , $I_D=20\text{A}$ $V_{DS}=50\text{V}$ |            | 80         |            | nC            |
| Gate Source Charge                | $Q_{gs}$     |                                                            |            | 23         |            |               |
| Gate Drain Charge                 | $Q_{gd}$     |                                                            |            | 17         |            |               |

**电性能参数 / Electrical Characteristics(Ta=25°C)**

| 参数<br>Parameter     | 符号<br>Symbol | 测试条件<br>Test Conditions                                        | 最小值<br>Min | 典型值<br>Typ | 最大值<br>Max | 单位<br>Unit |
|---------------------|--------------|----------------------------------------------------------------|------------|------------|------------|------------|
| Turn-On Delay Time  | $t_{d(on)}$  | $V_{GS}=10V$ $V_{DS}=50V$<br>$R_L=2.5\Omega$ $R_{GEN}=3\Omega$ |            | 25         |            | ns         |
| Turn-On Rise Time   | $t_r$        |                                                                |            | 17         |            |            |
| Turn-Off Delay Time | $t_{d(off)}$ |                                                                |            | 53         |            |            |
| Turn-Off Fall Time  | $t_f$        |                                                                |            | 24         |            |            |

## 电参数曲线图 / Electrical Characteristic Curve

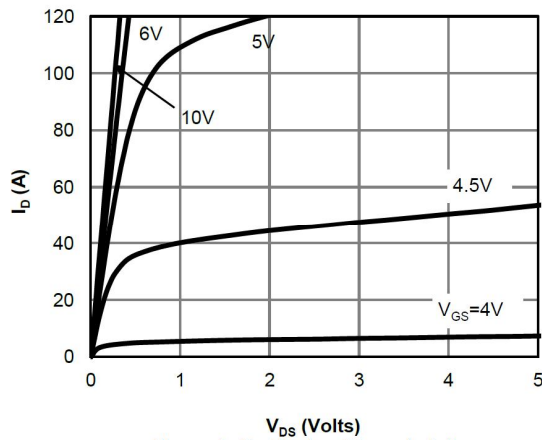


Figure 1: On-Region Characteristics

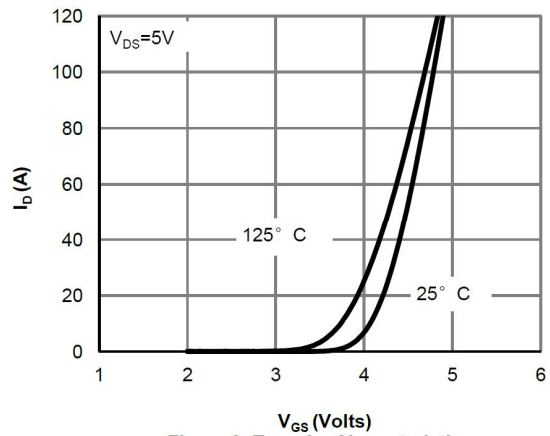


Figure 2: Transfer Characteristics

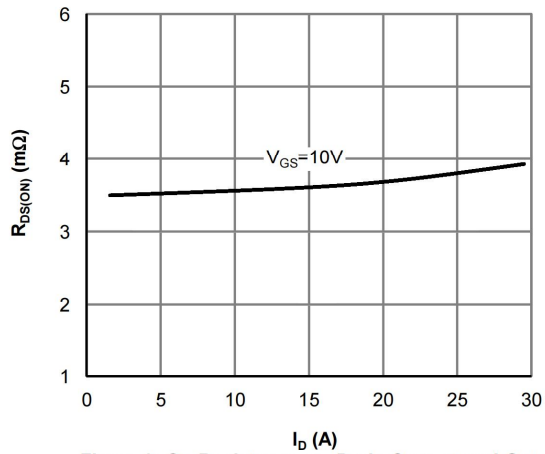


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

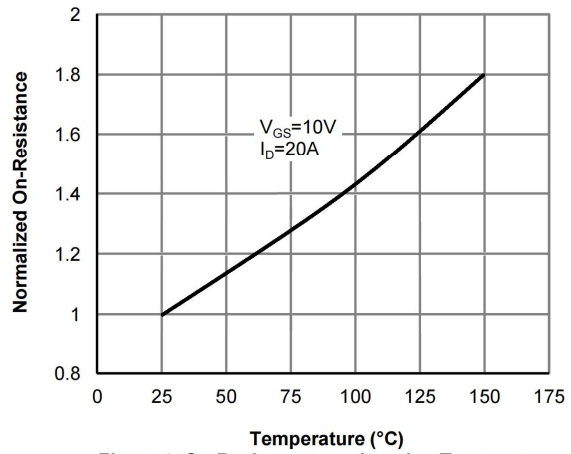


Figure 4: On-Resistance vs. Junction Temperature

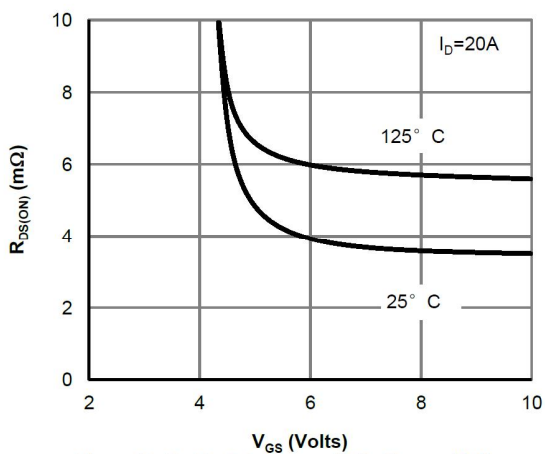


Figure 5: On-Resistance vs. Gate-Source Voltage

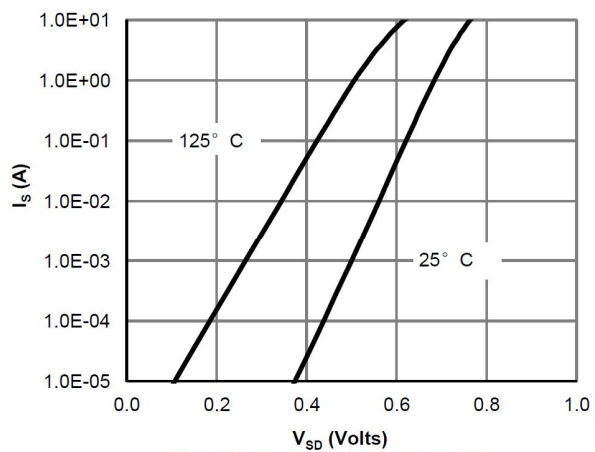
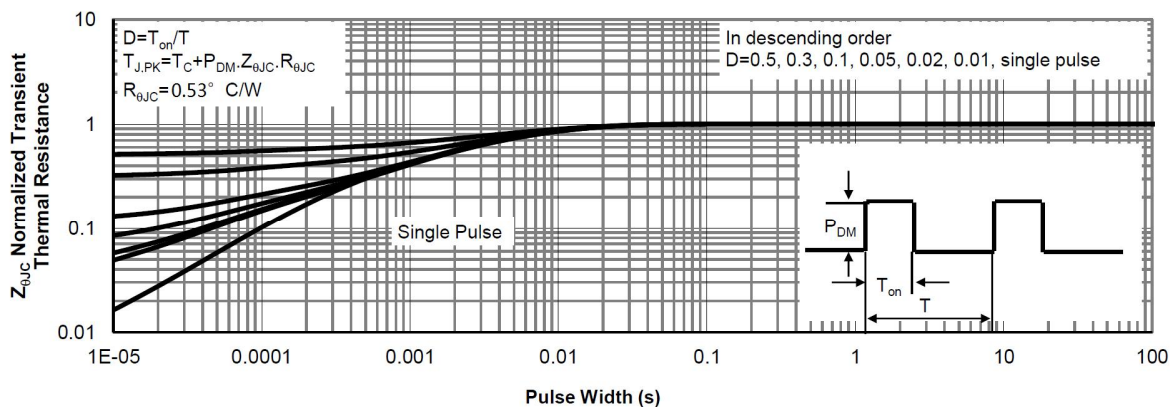
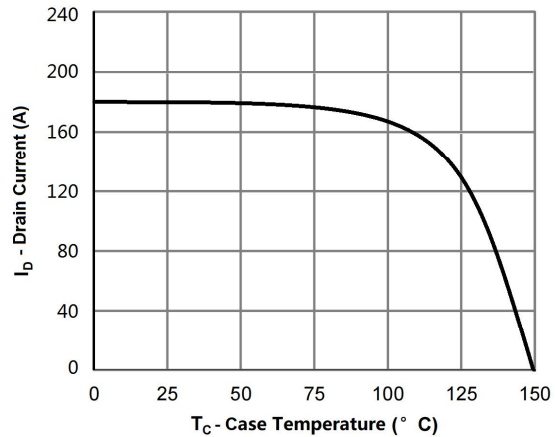
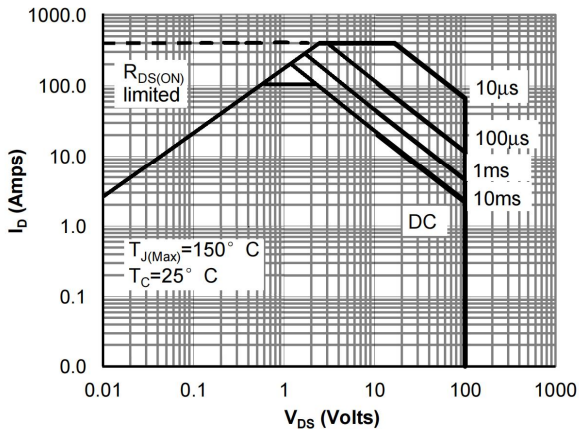
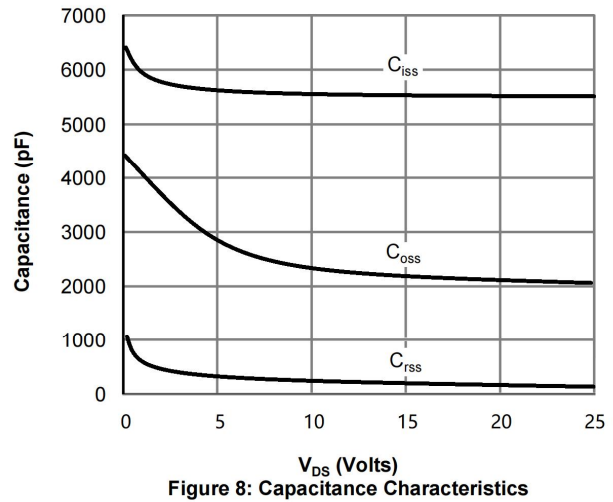
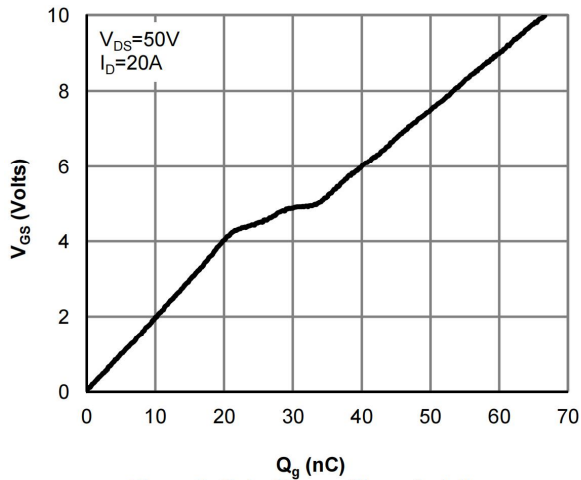
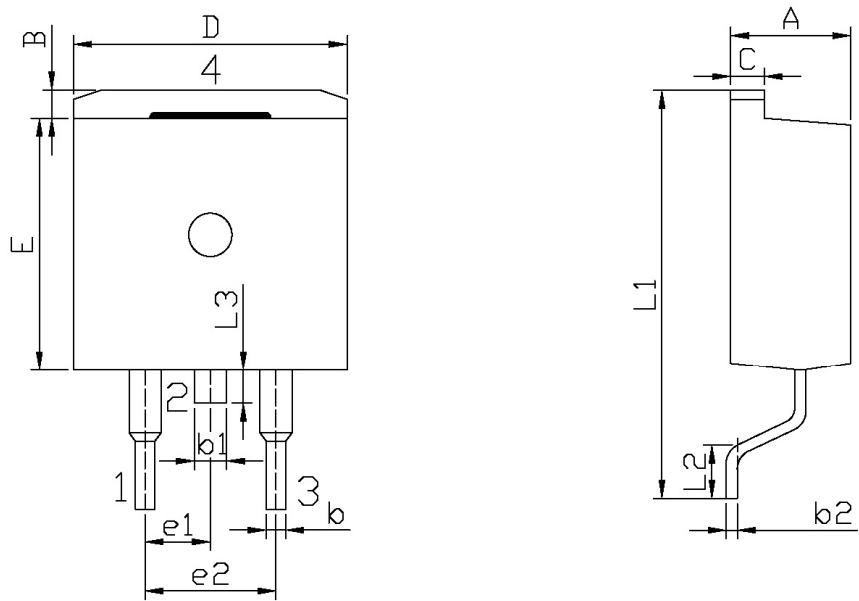


Figure 6: Body-Diode Characteristics

## 电参数曲线图 / Electrical Characteristic Curve



外形尺寸图 / Package Dimensions



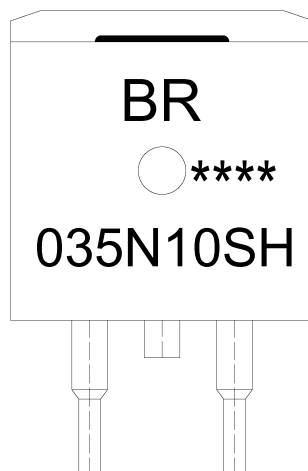
单位：mm

| Symbol | Dimensions In Millimeters |       | Symbol | Dimensions In Millimeters |       |
|--------|---------------------------|-------|--------|---------------------------|-------|
|        | Min                       | Max   |        | Min                       | Max   |
| A      | 4.30                      | 4.70  | E      | 9.00                      | 9.40  |
| B      | 1.00                      | 1.40  | e1     | 2.34                      | 2.74  |
| b      | 0.70                      | 0.90  | e2     | 4.88                      | 5.28  |
| b1     | 1.15                      | 1.35  | L1     | 15.00                     | 16.00 |
| b2     | 0.40                      | 0.60  | L2     | 2.24                      | 2.84  |
| C      | 1.20                      | 1.40  | L3     | 1.20                      | 1.60  |
| D      | 9.80                      | 10.20 |        |                           |       |

T0-263



**印章说明 / Marking Instructions**



说明：

BR： 为公司代码

035N10SH： 为型号代码

\*\*\*\*： 为生产批号代码，随生产批号变化

Note:

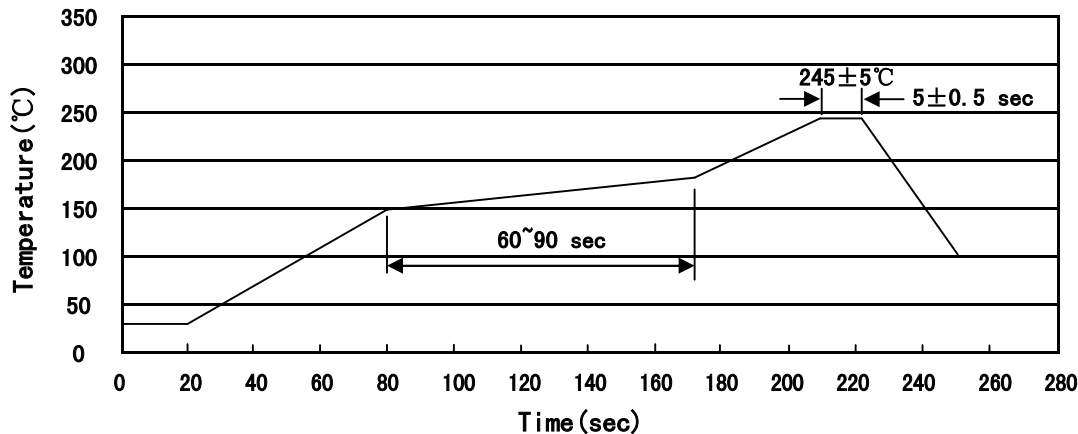
BR: Company Code

035N10SH: Product Type

\*\*\*\*: Lot No. Code, code change with Lot No



## 回流焊温度曲线图(无铅) / Temperature Profile for IR Reflow Soldering(Pb-Free)



说明：

- 1、预热温度 150~180°C，时间 60~90sec；
- 2、峰值温度 245±5°C，时间持续为 5±0.5sec；
- 3、焊接制程冷却速度为 2~10°C/sec.

Note:

- 1.Preheating:150~180°C, Time:60~90sec.
- 2.Peak Temp.:245±5°C, Duration:5±0.5sec.
3. Cooling Speed: 2~10°C/sec.

## 耐焊接热试验条件 / Resistance to Soldering Heat Test Conditions

温度：260±5°C

时间：10±1 sec.

Temp.:260±5°C

Time:10±1 sec

## 包装规格 / Packaging SPEC.

卷盘包装 / REEL

| Package Type<br>封装形式 | Units 包装数量         |                         |                        |                              |                        | Dimension 包装尺寸 (unit: mm <sup>3</sup> ) |             |             |
|----------------------|--------------------|-------------------------|------------------------|------------------------------|------------------------|-----------------------------------------|-------------|-------------|
|                      | Units/Reel<br>只/卷盘 | Reels/Inner Box<br>卷盘/盒 | Units/Inner Box<br>只/盒 | Inner Boxes/Outer Box<br>盒/箱 | Units/Outer Box<br>只/箱 | Reel                                    | Inner Box 盒 | Outer Box 箱 |
| TO-263               | 800                | 1                       | 800                    | 6                            | 4,800                  | 13" ×24                                 | 360×360×50  | 380×335×366 |

套管包装 / TUBE

| Package Type<br>封装形式 | Units 包装数量         |                         |                        |                              |                        | Dimension 包装尺寸 (unit: mm <sup>3</sup> ) |             |             |
|----------------------|--------------------|-------------------------|------------------------|------------------------------|------------------------|-----------------------------------------|-------------|-------------|
|                      | Units/Tube<br>只/套管 | Tubes/Inner Box<br>套管/盒 | Units/Inner Box<br>只/盒 | Inner Boxes/Outer Box<br>盒/箱 | Units/Outer Box<br>只/箱 | Tube 套管                                 | Inner Box 盒 | Outer Box 箱 |
| TO-263               | 50                 | 20                      | 1,000                  | 5                            | 5,000                  | 532×33×7.0                              | 555×164×50  | 575×290×180 |

## 使用说明 / Notices